

3469674 FAIRCHILD SEMICONDUCTOR

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A Schlumberger Company

PN5135/FTSO5135 T-29-23
PN5136/FTSO5136
PN5137/FTSO5137
 NPN Small Signal General Purpose Amplifiers

- P_D ... 625 mW @ $T_A = 25^\circ\text{C}$
- V_{CE0} ... 25 V (Min) (PN/FTSO5135)
- h_{FE} ... 50-600 @ 10 mA (PN/FTSO5135), 20-400 @ 150 mA (PN/FTSO5136/7)
- f_T ... 40 MHz (Min)
- Complements ... PN5142, PN5143

PACKAGE

PN5135	TO-92
PN5136	TO-92
PN5137	TO-92
FTSO5135	TO-236AA/AB
FTSO5136	TO-236AA/AB
FTSO5137	TO-236AA/AB

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

Power Dissipation (Notes 2 & 3)

Total Dissipation at	PN	FTSO
25° C Ambient Temperature	0.625 W	0.350 W*
25° C Case Temperature	1.0 W	

Voltages & Currents

	5135	5136/7
V_{CE0} Collector to Emitter Voltage (Note 4)	25 V	20 V
V_{CBO} Collector to Base Voltage	30 V	30 V
V_{CES} Collector to Emitter Voltage	30 V	30 V
V_{EBO} Emitter to Base Voltage	4.0 V	3.0 V
I_C Collector Current	200 mA	200 mA

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	5135		5136		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
BV_{CES}	Collector to Emitter Breakdown Voltage	30		30		V	$I_C = 100 \mu\text{A}, V_{BE} = 0$
BV_{CBO}	Collector to Base Breakdown Voltage	30		30		V	$I_C = 100 \mu\text{A}, I_E = 0$
BV_{EBO}	Emitter to Base Breakdown Voltage	4.0		3.0		V	$I_E = 10 \mu\text{A}, I_C = 0$
I_{EBO}	Emitter Cutoff Current		10		100	nA μA	$V_{EB} = 2.0 \text{ V}, I_C = 0$ $V_{EB} = 4.0 \text{ V}, I_C = 0$

NOTES:

1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
 2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations
 3. These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/°C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/°C).
 4. Rating refers to a high current point where collector to emitter voltage is lowest.
 5. Pulse conditions: length = 300 μs; duty cycle = 1%.
 6. For product family characteristic curves, refer to Curve Set T145.
- * Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

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PN5135/FTSO5135

PN5136/FTSO5136

PN5137/FTSO5137

T-29-23

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	5135		5136		UNITS	TEST CONDITIONS
		MIN	MAX	MIN	MAX		
I_{CBO}	Collector Cutoff Current	300	10		100	nA	$V_{CB} = 15\text{ V}, I_E = 0$ $V_{CB} = 20\text{ V}, I_E = 0$ $V_{CB} = 15\text{ V}, I_E = 0$ $T_A = 65^\circ\text{ C}$ $V_{CB} = 20\text{ V}, I_E = 0,$ $T_A = 65^\circ\text{ C}$
					10	nA	
						μA	
						μA	
h_{FE}	DC Pulse Current Gain (Note 5)	50	600				$I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 2.0\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 1.0\text{ V}$
		15		20	400		
				20			
$V_{CE(sus)}$	Collector to Emitter Sustaining Voltage (Notes 4 & 5)	25		20		V	$I_C = 1.0\text{ mA (pulsed)}, I_B = 0$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		1.0		0.25	V	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$ $I_C = 150\text{ mA}, I_B = 15\text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)		1.0		1.1	V	$I_C = 100\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}$
$V_{BE(sat)}$	Base to Emitter Saturation Voltage (Note 5)		1.0		1.1	V	$I_C = 100\text{ mA}, I_B = 10\text{ V}$ $I_C = 150\text{ mA}, I_B = 15\text{ V}$
C_{cb}	Collector to Base Capacitance		25		35	pF	$V_{CB} = 10\text{ V}, I_E = 0, f = 1.0\text{ MHz}$
C_{eb}	Emitter to Base Capacitance				85	pF	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1.0\text{ MHz}$
$ h_{fe} $	Magnitude of Common Emitter Small Signal Current Gain	2.0	15	2.0	20		$I_C = 30\text{ mA}, V_{CE} = 10\text{ V},$ $f = 20\text{ MHz}$ $I_C = 50\text{ mA}, V_{CE} = 5.0\text{ V},$ $f = 20\text{ MHz}$

SYMBOL	CHARACTERISTIC	5137		UNITS	TEST CONDITIONS
		MIN	MAX		
BV_{CES}	Collector to Emitter Breakdown Voltage	30		V	$I_C = 100\text{ }\mu\text{A}, V_{BE} = 0$
BV_{CBO}	Collector to Base Breakdown Voltage	30		V	$I_C = 100\text{ }\mu\text{A}, I_E = 0$
BV_{EBO}	Emitter to Base Breakdown Voltage	3.0		V	$I_E = 10\text{ }\mu\text{A}, I_C = 0$
I_{EBO}	Emitter Cutoff Current		100	nA	$V_{EB} = 2.0\text{ V}, I_C = 0$
I_{CBO}	Collector Cutoff Current		100	nA	$V_{CB} = 20\text{ V}, I_E = 0$ $V_{CB} = 20\text{ V}, I_E = 0,$ $T_A = 65^\circ\text{ C}$
			10	μA	
h_{FE}	DC Pulse Current Gain (Note 5)	20	400		$I_C = 150\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 30\text{ mA}, V_{CE} = 1.0\text{ V}$
		20			

FAIRCHILD SEMICONDUCTOR

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3469674 FAIRCHILD SEMICONDUCTOR

84D 27461 D

PN5135/FTSO5135
 PN5136/FTSO5136
 PN5137/FTSO5137

T-29-23

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	5137		UNITS	TEST CONDITIONS
		MIN	MAX		
$V_{CE(sus)}$	Collector to Emitter Sustaining Voltage (Notes 4 & 5)	20		V	$I_C = 1.0 \text{ mA}$ (pulsed), $I_B = 0$
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		0.25	V	$I_C = 150 \text{ mA}$, $I_B = 15 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)		1.1	V	$I_C = 150 \text{ mA}$, $V_{CE} = 1.0 \text{ V}$
$V_{BE(sat)}$	Base to Emitter Saturation Voltage (Note 5)		1.1	V	$I_C = 150 \text{ mA}$, $I_B = 15 \text{ V}$
C_{cb}	Collector to Base Capacitance		35	pF	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$
C_{eb}	Emitter to Base Capacitance		85	pF	$V_{BE} = 0.5 \text{ V}$, $I_C = 0$, $f = 1.0 \text{ MHz}$
$ h_{re} $	Magnitude of Common Emitter Small Signal Current Gain	2.0	20		$I_C = 50 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$, $f = 20 \text{ MHz}$



PN5138/FTSO5138

PNP Low Level Amplifier

T-29-23

- $h_{FE} \dots 50$ (Min) @ 100 μ A & 10 mA
- $V_{CEO} \dots -30$ V (Min)

PACKAGE

PN5138
FTSO5138

TO-92
TO-236AA/AB

ABSOLUTE MAXIMUM RATINGS (Note 1)**Temperatures**

Storage Temperature -55°C to 150°C
Operating Junction Temperature 150°C

Power Dissipation (Notes 2 & 3)

	PN	FTSO
Total Dissipation at		
25 $^{\circ}$ C Ambient Temperature	0.625 W	0.350 W*
25 $^{\circ}$ C Case Temperature	1.0 W	

Voltages & Currents

V_{CEO} Collector to Emitter Voltage	-30 V
V_{CBO} Collector to Base Voltage	-30 V
V_{EBO} Emitter to Base Voltage	-5.0 V

ELECTRICAL CHARACTERISTICS (25 $^{\circ}$ C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
BV_{CBO}	Collector to Base Breakdown Voltage	-30		V	$I_C = 100 \mu\text{A}$, $I_E = 0$
BV_{EBO}	Emitter to Base Breakdown Voltage	-5.0		V	$I_E = 100 \mu\text{A}$, $I_C = 0$
I_{CBO}	Collector Cutoff Current		50 3.0	nA μA	$V_{CB} = -20$ V, $I_E = 0$ $V_{CB} = -20$ V, $I_E = 0$, $T_A = 65^{\circ}\text{C}$
h_{FE}	DC Current Gain	50 50	800		$I_C = 100 \mu\text{A}$, $V_{CE} = -10$ V $I_C = 1.0$ mA, $V_{CE} = -10$ V
h_{FE}	DC Pulse Current Gain (Note 5)	50			$I_C = 10$ mA, $V_{CE} = -10$ V
$V_{CEO(\text{sub})}$	Collector to Emitter Sustaining Voltage (Notes 4 & 5)	-30		V	$I_C = 10$ mA (pulsed), $I_B = 0$

NOTES:

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
 - These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 - These ratings give a maximum junction temperature of 150 $^{\circ}$ C and (TO-92) junction-to-case thermal resistance of 125 $^{\circ}$ C/W (derating factor of 8.0 mW/ $^{\circ}$ C); junction-to-ambient thermal resistance of 200 $^{\circ}$ C/W (derating factor of 5.0 mW/ $^{\circ}$ C); (TO-236) junction-to-ambient thermal resistance of 357 $^{\circ}$ C/W (derating factor of 2.8 mW/ $^{\circ}$ C).
 - Rating refers to a high current point where collector to emitter voltage is lowest.
 - Pulse conditions: length = 300 μ s; duty cycle = 1%.
 - For product family characteristic curves, refer to Curve Set T219.
- * Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

PN5138/FTSO5138

T-29-23

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Note 5)		-0.3	V	$I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$
$V_{BE(ON)}$	Base to Emitter "On" Voltage (Note 5)		-1.0	V	$I_C = 10 \text{ mA}$, $V_{CE} = -10 \text{ V}$
$V_{BE(sat)}$	Base to Emitter Saturation Voltage (Note 5)		-1.0	V	$I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$
C_{cb}	Collector to Base Capacitance		7.0	pF	$V_{CB} = -5.0 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$
C_{eb}	Emitter to Base Capacitance		30	pF	$V_{EB} = -5.0 \text{ V}$, $I_C = 0$, $f = 1.0 \text{ MHz}$
h_{fe}	High Frequency Current Gain	1.5			$I_C = 0.5 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 20 \text{ MHz}$
h_{fe}	Small Signal Current Gain	40	1000		$I_C = 1.0 \text{ mA}$, $V_{CE} = -10 \text{ V}$, $f = 1.0 \text{ kHz}$

FAIRCHILD

A Schlumberger Company

PN5139/FTSO5139PNP Small Signal General Purpose
Amplifier & Switch

T-29-23

- V_{CE0} ... -20 V (Min)
- h_{FE} ... 40 (Min) @ 10 mA
- f_T ... 300 MHz (Min)
- C_{cb} ... 5.0 pF (Max) @ -10 V

PACKAGE

PN5139

TO-92

FTSO5139

TO-236AA/AB

ABSOLUTE MAXIMUM RATINGS (Note 1)**Temperatures**

Storage Temperature	-55° C to 150° C
Operating Junction Temperature	150° C

Power Dissipation (Notes 2 & 3)

Total Dissipation at	PN	FTSO
25° C Ambient Temperature	0.625 W	0.350 W*
25° C Case Temperature	1.0 W	

Voltages & Currents

V_{CE0} Collector to Emitter Voltage	-20 V
(Note 4)	
V_{CBO} Collector to Base Voltage	-20 V
V_{EBO} Emitter to Base Voltage	-5.0 V
I_C Collector Current	100 mA

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
BV_{CBO}	Collector to Base Breakdown Voltage	-20		V	$I_C = 100 \mu A, I_E = 0$
BV_{CES}	Collector to Emitter Breakdown Voltage	-20		V	$I_C = 100 \mu A, V_{EB} = 0$
BV_{EBO}	Emitter to Base Breakdown Voltage	-5.0		V	$I_E = 100 \mu A, I_C = 0$
I_{CES}	Collector Reverse Current		50 25	nA μA	$V_{CE} = -15 V, V_{EB} = 0$ $V_{CE} = -15 V, V_{EB} = 0, T_A = 65^\circ C$
h_{FE}	DC Current Gain	30 40			$I_C = 100 \mu A, V_{CE} = -10 V$ $I_C = 1.0 mA, V_{CE} = -10 V$
h_{FE}	DC Pulse Current Gain (Note 5)	40 15			$I_C = 10 mA, V_{CE} = -1.0 V$ $I_C = 50 mA, V_{CE} = -10 V$

NOTES:

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
 - These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 - These ratings give a maximum junction temperature of 150° C and (TO-92) junction-to-case thermal resistance of 125° C/W (derating factor of 8.0 mW/° C); junction-to-ambient thermal resistance of 200° C/W (derating factor of 5.0 mW/° C); (TO-236) junction-to-ambient thermal resistance of 357° C/W (derating factor of 2.8 mW/° C).
 - Rating refers to a high current point where collector to emitter voltage is lowest.
 - Pulse conditions: length = 300 μs ; duty cycle = 1%.
 - For product family characteristic curves, refer to Curve Set T215.
- * Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

PN5139/FTSO5139

T-29-23

ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage		-0.15	V	$I_C = 1.0 \text{ mA}$, $I_B = 0.1 \text{ mA}$
$V_{CE(sat)}$	Pulsed Collector to Emitter Saturation Voltage (Note 5)		-0.20 -0.5	V V	$I_C = 10 \text{ mA}$, $I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}$, $I_B = 5.0 \text{ mA}$
$V_{BE(sat)}$	Pulsed Base to Emitter Saturation Voltage (Note 5)	-0.7 -0.75	-1.0 -1.25	V V	$I_C = 10 \text{ mA}$, $I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}$, $I_B = 5.0 \text{ mA}$
$V_{CE(sust)}$	Collector to Emitter Sustaining Voltage (Note 5)	-20		V	$I_C = 10 \text{ mA}$ (pulsed), $I_B = 0$
C_{cb}	Collector to Base Capacitance		5.0	pF	$V_{CB} = -10 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$
C_{eb}	Emitter to Base Capacitance		8.0	pF	$V_{EB} = -0.5 \text{ V}$, $I_C = 0$, $f = 1.0 \text{ MHz}$
$ h_{fe} $	Magnitude of Small Signal Current Gain	3.0			$I_C = 10 \text{ mA}$, $V_{CE} = -20 \text{ V}$, $f = 100 \text{ MHz}$
t_{on}	Turn On Time (test circuit no. 407)		50	ns	$I_C \approx 50 \text{ mA}$, $I_{B1} \approx 5.0 \text{ mA}$
t_{off}	Turn Off Time (test circuit no. 407)		200	ns	$I_C \approx 50 \text{ mA}$, $I_{B1} \approx 5.0 \text{ mA}$, $I_{B2} \approx -5.0 \text{ mA}$



1N456/457/458/459 T-01-09
FDLL456/457/458/459
1N456A/457A/458A/459A
FDLL456A/457A/458A/459A
 Low Leakage Diodes

- $I_R \dots 25 \text{ nA (MAX) @ WIV}$
- $C \dots 6.0 \text{ pF (MAX)}$

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature Range	-65°C to +200°C
Maximum Junction Operating Temperature	+175°C
Lead Temperature	+260°C

Power Dissipation (Note 2)

Maximum Total Power Dissipation at 25°C Ambient	500 mW
Linear Power Derating Factor (From 25°C)	3.33 mW/°C

Maximum Voltage and Currents

	1N456/A	1N457/A	1N458/A	1N459/A
WIV Working Inverse Voltage	25 V	60 V	125 V	175 V
I_O Average Rectified Current				200 mA
I_F Continuous Forward Current				500 mA
i_f Peak Repetitive Forward Current				600 mA
$i_f(\text{surge})$ Peak Forward Surge Current				4.0 A
				1.0 A
				Pulse Width = 1 μ s
				Pulse Width = 1 s

PACKAGES

1N456	DO-35
1N457	DO-35
1N458	DO-35
1N459	DO-35
1N456A	DO-35
1N457A	DO-35
1N458A	DO-35
1N459A	DO-35
FDLL456	LL-34
FDLL457	LL-34
FDLL458	LL-34
FDLL459	LL-34
FDLL456A	LL-34
FDLL457A	LL-34
FDLL458A	LL-34
FDLL459A	LL-34

If you need this device in the SOT package, an electrical equivalent is available. See FDSO1500 family.

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_F	Forward Voltage 1N456A/7A/8A/9A		1.0	V	$I_F = 100 \text{ mA}$ $I_F = 40 \text{ mA}$ $I_F = 20 \text{ mA}$ $I_F = 7 \text{ mA}$ $I_F = 3 \text{ mA}$
		1N456	1.0	V	
		1N457	1.0	V	
		1N458	1.0	V	
		1N459	1.0	V	
I_R	Reverse Current		25	nA	$V_R = \text{Rated WIV}$ $V_R = \text{Rated WIV}, T_A = 150^\circ\text{C}$
			5.0	μA	
BV	Breakdown Voltage	1N456/A	30	V	$I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$
		1N457/A	70	V	
		1N458/A	150	V	
		1N459/A	200	V	
C	Capacitance		6.0	pF	$V_R = 0, f = 1 \text{ MHz}$

NOTES:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
3. For product family characteristic curves, refer to Chapter 4, D2.



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1N461A/462A/463A
FDLL461A/462A/463A

General Purpose High
Conductance Diodes

T-01-09

- $V_F \dots 1.0 \text{ V (MAX) @ } 100 \text{ mA}$
- $I_R \dots 500 \text{ nA (MAX) @ WIV}$

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature Range	-65°C to +200°C
Maximum Junction Operating Temperature	+175°C
Lead Temperature	+260°C

Power Dissipation (Note 2)

Maximum Total Power Dissipation at 25°C Ambient	500 mW
Linear Power Derating Factor (from 25°C)	3.33 mW/°C

Maximum Voltage and Currents

	IN461A	IN462A	IN463A	IN464A
WIV Working Inverse Voltage	25 V	60 V	175 V	125 V
I_O Average Rectified Current	200 mA	200 mA	200 mA	200 mA
I_F Continuous Forward Current	500 mA	500 mA	500 mA	500 mA
i_f Peak Repetitive Forward Current	600 mA	600 mA	600 mA	600 mA
$i_f(\text{surge})$ Peak Forward Surge Current				
Pulse Width = 1 s	1.0 A	1.0 A	1.0 A	1.0 A
Pulse Width = 1 μ s	4.0 A	4.0 A	4.0 A	4.0 A

PACKAGES

1N461A	DO-35
1N462A	DO-35
1N463A	DO-35
FDLL461A	LL-34
FDLL462A	LL-34
FDLL463A	LL-34

If you need this device in the SOT package, an electrical equivalent is available. See FDSO1500 family.



ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_F	Forward Voltage		1.0	V	$I_f = 100 \text{ mA}$
I_R	Reverse Current		500 30	nA μ A	$V_R = \text{Rated WIV}$ $V_R = \text{Rated WIV}, T_A = 150^\circ\text{C}$
BV	Breakdown Voltage	IN461A IN462A IN463A IN464A	30 70 200 150	V	$I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$ $I_R = 100 \mu\text{A}$

NOTES:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
3. For product family characteristic curves, refer to Chapter 4, D2.



1N482B/483B/484B/485B
FDLL482B/483B/484B/485B

General Purpose Low
 Leakage Diodes

T-01-09

- V_F ... 1.0 V (MAX) @ 100 mA
- I_R ... 25 nA (MAX) @ WIV

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature Range	-65°C to +200°C
Maximum Junction Operating Temperature	+175°C
Lead Temperature (from 25°C)	+260°C

Power Dissipation (Note 2)

Maximum Total Power Dissipation at 25°C Ambient	500 mW
Linear Power Derating Factor (from 25°C)	3.33 mW/°C

Maximum Voltage and Currents

	1N482B	1N483B	1N484B	1N485B	1N486B
WIV Working Inverse Voltage	36 V	70 V	130 V	180 V	225 V
I_O Average Rectified Current					200 mA
I_F Continuous Forward Current					500 mA
I_f Peak Repetitive Forward Current					600 mA
$I_f(\text{surge})$ Peak Forward Surge Current					
Pulse Width = 1 s					1.0
Pulse Width = 1 μ s					4.0

PACKAGES

1N482B	DO-35
1N483B	DO-35
1N484B	DO-35
1N485B	DO-35
FDLL482B	LL-34
FDLL483B	LL-34
FDLL484B	LL-34
FDLL485B	LL-34

If you need this device in the SOT package, an electrical equivalent is available. See FDSO1500 family.

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_F	Forward Voltage		1.0	V	$I_F = 100$ mA
I_R	Reverse Current	1N482B - 1N485B	25	nA	$V_R = \text{Rated WIV}$ $V_R = \text{Rated WIV}, T_A = 150^\circ\text{C}$ $V_R = 225$ V $V_R = 225$ V, $T_A = 150^\circ\text{C}$
		1N486B	5.0	μ A	
		50	nA		
		10	μ A		
BV	Breakdown Voltage	1N482B	40	V	$I_R = 100$ μ A
		1N483B	80	V	$I_R = 100$ μ A
		1N484B	150	V	$I_R = 100$ μ A
		1N485B	200	V	$I_R = 100$ μ A
		1N486B	250	V	$I_R = 100$ μ A

NOTES:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
3. For product family characteristic curves, refer to Chapter 4, D2.